

a one-step graded structure, each period of such bottom mirror being with a structure of $\text{Al}_{0.14}\text{Ga}_{0.86}\text{As}(500\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})/\text{AlAs}(500\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})$ where $1\text{\AA}=10^{-10}\text{m}$. Alternatively, the mirror structure may be provided with linear grading or with a superlattice grading of the stack.

Confining layers 14 and 16 are provided to confine active region 15 and to adjust the length (L) of the optical cavity. This optical cavity length should be $2L=N\lambda$, wherein N is an integer and λ is an operating optical wavelength of the laser. To obtain constructive interference, the thickness of the confining layers should be a multiple of $\lambda/2$ or $\lambda/4$. Typically, the thickness of each confining layer ranges from 0 to 3 μm . The confining regions are $\text{Al}_x\text{Ga}_{1-x}\text{As}$, with x ranging from 0.1 to 0.4.

Active region 15 is a region in which electrons (-) and holes (+) recombine providing, under proper stimulation, a lasing emission. The active region with a thickness ranging from 0.1 to 1 μm , is a multi-quantum well (MQW) structure with very thin barriers. Each quantum well includes a narrow gap semiconductor 1 to 30 nm thick, confined by wide-gap semiconductor about 1 to 20 nm in thickness.

The second quarter-wave stack of from 2 to 20 pairs or periods of high index/low index material layers similar to the pairs or periods in bottom mirror 13, but with p⁺-type doping (1×10^{18} to $5\times 10^{19}\text{ cm}^{-3}$), forms multilayer DBR top mirror 17 upon confining layer 16. The peripheral region of the top mirror includes ion-implanted region 18. The ions are implanted into the peripheral region of top mirror 17, creating window 19 so that both the current and the lasing emission are confined to a narrow centrally located region. The ions are selected from ions of elements which do not affect the conductivity type of the material in which they are implanted. Ions, such as H^+ or O^+ , are implanted in concentrations ranging from 1×10^{18} to 5×10^{19} per cm^3 .

A thin layer 20 of dielectric material, such as SiO_2 , Si_3N_4 , Vycor® glass, etc., is formed upon top mirror 17 with a thickness ranging from 0.01 to 0.1 μm . Layer 20 has a centrally located window 21 which is substantially coextensive with window 19 formed in the ion-implanted area 18. Windows 19 and 21 cooperate in restricting the laser emission to the centrally located region. Layer 20 also permits passage of operating current only through window 21, thus restricting the current flow to a narrow area of the active region. Each of the windows is from 5 to 50 μm , preferably 10 to 20 μm , in diameter.

Optically transparent top electrode 23 is deposited as a layer on top of the structure with lasing emission from active layer 15 taking place through the top mirror and through the top electrode. In accordance with this invention, the electrode material is selected from optically transmissive semiconductor materials having conductivities ranging from 1×10^3 to

$1\times 10^5\Omega^{-1}\text{cm}^{-1}$, light transmissivity greater than 80 percent and light absorption of less than 10 percent. The optically transmissive semiconductor layer is applied in the laser structure onto the top mirror to serve as the vertical-injection contact without substantially interfering with the light output. Cadmium tin oxide (CTO) and indium tin oxide (ITO), with the respective nominal formula $\text{Cd}_{2-x}\text{Sn}_x\text{O}_4$ with x ranging from 0.01 to 0.5, preferably from 0.3 to 0.4, and $\text{In}_{2-y}\text{Sn}_y\text{O}_3$, with y ranging from 0.01 to 0.2, are especially suitable for this purpose. The cadmium tin oxide is optically transparent (greater than 80 percent) with a negligible absorption (<1%) and is electrically conductive with a conductivity of $2\times 10^3\Omega^{-1}\text{cm}^{-1}$ and resistivity of $5\times 10^{-4}\Omega\text{cm}$ at room temperature. The indium tin oxide is also optically transparent (greater than 90 percent) with a very small absorption (<5%) and is electrically conductive with a conductivity of $2.5\times 10^3\Omega^{-1}\text{cm}^{-1}$ and resistivity of $4\times 10^{-4}\Omega\text{cm}$ at room temperature. These materials, when deposited in thickness ranging from 50 nm to 500 nm, preferably from 200 to 300 nm, provide electrical conductivity sufficient for use as an electrode of the laser and yet exhibit transparent properties with transmissivity (T) greater than 80 percent and absorption <10 percent.

Prior to the deposition of top electrode 23, a thin metal barrier layer 22 is deposited on top of the dielectric layer 20 and on that portion of top mirror 17 which is exposed in window 21. This barrier layer is deposited in a thickness of up to 300 $\text{\AA}$, preferably from 10 to 50 $\text{\AA}$. The barrier layer is used to avoid formation of another p-n junction between the p-type conductivity top mirror 17 and n-type conductivity semiconductor top electrode 23, which could interfere with the lasing emission. The barrier layer is selected from metals or alloys which do not cause contamination of the materials of the device, are capable of forming a non-alloyed ohmic contact with the surface of top mirror 17 and when deposited within the above thickness range do not substantially interfere with the transmission of the lasing emission.

Optionally, if the conductivity of an uppermost layer of top mirror 17 is insufficient to form a non-alloyed ohmic contact to barrier layer 22, a thin highly doped contacting layer(not shown) may be provided intermediate top mirror 17 and barrier layer 22 with a thickness ranging from 0.01 to 0.1 μm , preferably about 0.0625 μm , to facilitate establishment of the non-alloyed ohmic contact between the top mirror and the barrier metal layer. Typically, the doping concentration in the optional contacting layer would range from 1×10^{19} to $1\times 10^{20}\text{ cm}^{-3}$, preferably about $5\times 10^{19}\text{ cm}^{-3}$.

Metal electrode 11 ranging from 1 to 10 μm in thickness is formed on the bottom surface of substrate 12 to provide for current flow perpendicularly through the active region to cause lasing emission. Indium is a metal which may be deposited as a thin layer

without causing undue heating of the structure. The laser maybe mounted with electrode 11 in contact with a heat-sink plate, e.g. of copper or some other heat-conductive material which does not contaminate the laser materials.

Semiconductor layers 13 through 17 can be grown upon substrate 12 by such known methods as metal organic vapor phase epitaxy (MOVPE) or by molecular beam epitaxy (MBE) or by hydride vapor phase epitaxy (VPE). In the preferred embodiment, the VCSEL structures are grown by Molecular Beam Epitaxy (MBE) technology in a Varian Gen II or Riber MBE system on heavily doped (1×10^{17} – $4 \times 10^{18} \text{ cm}^{-3}$) substrates 12. After layers 13 through 17 are grown, windows 19 and 21 are defined by photolithographic technique by depositing a suitable resist on the centrally located upper surface of top mirror 17. The partially formed structure with resist thereon is transferred to a separate high vacuum chamber where the structure is subjected to ion implantation, e.g. H^+ or O^+ , to form ion-implanted region 18. After dielectric layer 20 is formed on the upper surface of top mirror 17 and the resist is removed, thin metal barrier layer 22 is deposited on top of the dielectric layer and on the upper surface of top mirror 17 exposed in window 21. Such a metal layer is conveniently deposited by evaporation at temperatures ranging from 100 to 500°C , preferably from 100 to 250°C , by sputtering or by electron-beam deposition. The latter process is preferable since the higher temperatures needed for evaporation could result in undesirable alloying of the metal into the semiconductor leading to a rough interface morphology which degrades the reflection properties of the mirror. After the deposition of the barrier layer, optically transparent semiconductor top electrode 23 is deposited on top of the structure. The top electrode is deposited with a thickness sufficient to enable the semiconductor material of the electrode to act as a terminal conductor for the device and yet insufficient to effectively reduce lasing emission from the top mirror. For such semiconductor materials as cadmium tin oxide and indium tin oxide, an effective thickness falls within a range of from 50 nm to 500 nm. Thin bottom electrode layer 11, e.g., of In, may then be formed on the bottom surface of substrate 12. Finally, the bottom or substrate side of the laser may be mounted via the In electrode or by means of a conductive adhesive, such as epoxy, on a copper slab which serves as a heat sink in common to other devices.

In the preferred embodiment, the VCSEL is an $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ with x being defined appropriately hereinbelow for each semiconductor layer of the structure. The laser structure comprises in an ascending sequence a 1 to 2 μm thick In electrode 11, a 500 μm thick (001)-oriented heavily doped ($2 \times 10^{18} \text{ cm}^{-3}$) n^+ -GaAs substrate 12, bottom mirror 13 consisting of a quarter-wave stack of 30 periods of n^+ -type semiconductor layers forming the multilayer dis-

tributed Bragg reflector (DBR) bottom mirror. Each period of the bottom mirror is of an one-step graded structure of $\text{Al}_{0.14}\text{Ga}_{0.86}\text{As}(500\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})/\text{AlAs}(580\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})$. It is Si-doped with a doping concentration of $3 \times 10^{18} \text{ cm}^{-3}$ near the substrate, which is then reduced to $1 \times 10^{18} \text{ cm}^{-3}$ in the last 6-10 periods near the active layer. The reflectivity spectrum of the DBR structure (bottom mirror 13) with the one-step graded structure, as measured with a Perkin-Elmer Lambda 9 UV/VIS/NIR Spectrophotometer, showed a broad high reflectivity band centered at $\sim 0.87 \mu\text{m}$ with a reflectivity > 99 percent, which matches a calculated reflectivity curve very well.

The bottom mirror is followed by n^+ -confinement layer 14, a p^- -active region layer 15 of four GaAs/AlGaAs quantum well structures about 0.1 μm total thickness and n^+ -confinement layer 16. Each of the confinement layers is about 820 $\text{\AA}$ thick. The GaAs/AlGaAs four quantum well structures of the active region are grown in a Riber MBE system. The active region is undoped, and consists of four 100 $\text{\AA}$ GaAs quantum wells with 70 $\text{\AA}$ $\text{Al}_{0.3}\text{Ga}_{0.7}\text{As}$ barriers. The active region is clad on the top and bottom by respective confinement layers 14 and 16. One-third of each confinement layer near the active region is undoped, and the rest is lightly doped (1×10^{18} – 1×10^{17}). Each confinement layer is linearly graded $\text{Al}_x\text{Ga}_{1-x}\text{As}$ with x graded from 0.3 to 0.57 near the mirrors. This graded-index, separate-confinement heterostructure helps the carrier confinement and reduces the lasing threshold current.

P-type top mirror 17 is a 20-period semiconductor mirror, which is also one-step graded to reduce the series resistance. Each period of the top mirror has a structure of $\text{Al}_{0.14}\text{Ga}_{0.86}\text{As}(500\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})/\text{AlAs}(580\text{\AA})/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}(100\text{\AA})$. It is Be-doped with a doping concentration of $5 \times 10^{18} \text{ cm}^{-3}$ in the first 16 periods. Then, the dopant concentration is increased to $2 \times 10^{19} \text{ cm}^{-3}$ near its upper surface to facilitate contacting.

At this fabrication stage the incomplete laser structure may be examined with the reflectivity measurement using an Anritsu MS9001B optical spectrum analyzer. The reflectivity measurements show Fabry-Perot resonance as a clear dip in the stop band. Then, ion-implanted region 18 is formed by implanting 300 keV H^+ ions (or 2000 keV O^+ ions) with a dose of $1 \times 10^{16} \text{ cm}^{-2}$ into top mirror 17 with a 10-20 μm diameter window protected by 6.2 μm thick photoresist (e.g. Shipley AZ Photoresist 4200). Upon formation of the ion-implanted region 18, and with the photoresist still in place, a 500 to 5000 $\text{\AA}$, preferably 1000 to 2000 $\text{\AA}$, thick SiO_2 layer 20 is grown on the surface of the top mirror layer at 100°C in a high vacuum chamber by electron beam evaporation. Thereafter the photo resist is stripped with acetone, and after the SiO_2 layer and that surface of the top mirror

which is exposed in window 21 are plasma cleaned, a silver layer, from 10 to 50 Å thick, is deposited (preferably by evaporation) upon the SiO₂ layer and also on the exposed surface of the top mirror.

Electrode 23 of cadmium tin oxide (or indium tin oxide) is formed on top of barrier electrode 22 with a thickness from about 50 to 500 nm, preferably 200 to 300 nm. In this thickness range, electrode 23 is sufficiently optically transparent to the lasing emission enabling its use as a top electrode of the VCSEL. Thicknesses higher than 500 nm may result in an increased series resistance without any improvement in the lasing efficiency.

The growth of the optically transparent semiconductor layer 23 uses an RF magnetron sputtering system (Anelva Corp., Model SPF-332H). In an exemplary embodiment, the target was a sintered disk (3 inches in diameter, 1/4 inch in thickness) of a mixture of about 67% CdO and about 33% SnO₂ (Haselden, San Jose, CA). The target was mounted 5cm above the samples. The plate voltage was 1.5 K V and the plate current approximately 110 mA. A deposition rate of 3Å/sec was maintained during the growth. The sputtering gas was a mixture of argon and oxygen at a total pressure of from 3 to 4 Pa. The resistivity of cadmium tin oxide (CTO) film depends strongly on the partial pressure of oxygen. Minimum resistivity is obtained for an oxygen partial pressure P_{O₂} of about 2-4×10⁻²Pa in 2-4 Pa argon. The cadmium tin oxide film was deposited in a thickness of ~2000Å. It has negligible absorption (less than 1%, which is limited by the capability of the setup) at 0.85μm. The resistivity of this film is ~5×10⁻⁴Ω-cm. For the above target, voltage, current and argon pressure it was found that the resistivity increases rapidly for P_{O₂} of 1×10⁻² and higher. A standard buffered oxide etchant was used to etch the deposited cadmium tin oxide layer in the process of device isolation. A top electrode of indium tin oxide (ITO) material may be produced in a similar manner.

Before characterizing the lasing properties, the substrate side of the sample is bonded with conductive epoxy on a copper slab which serves as a heat sink. No other cooling is used. All the experiments are done at room temperature. A fine probe is used to electrically contact and pump the lasers. Current is vertically injected through the window area, as shown by straight arrows in FIG. 1, and the remaining area of the device surface is electrically isolated from the top electrode with the SiO₂ layer 20.

FIG. 2 is the continuous wave light output power versus direct current. The light output power is measured with an ANDO AQ-1125 optical power meter calibrated at 0.85μm. The lasing threshold current is 4.2mA with ~35% external differential quantum efficiency at a lasing wavelength of ~0.85μm. Threshold currents as low as 3.8mA are obtainable. 50 Å thick

barrier layer 22 causes a small reduction in the laser output power (about 10%). FIG. 3 is the current-voltage curve which shows a voltage of 5.4V and a differential series resistance of 430Ω at the lasing threshold of 4.2 mA. FIG. 4 shows the far field light intensity distribution measured at a detector-sample distance of 8.3cm. The distribution is Gaussian-like, indicating a single fundamental transverse mode operation, with a full width at half maximum of 7.0°. Measurement is performed at stepped intervals of ~0.35° each, with a resolution of better than 0.2°.

It is also possible to fabricate a structure, not in accordance with the present invention, without the ion implantation region 18. In such a case, top mirror 17 is mesa-etched, and probed directly at the top window area. A device with a 40μm diameter mesa gives a pulsed (100ns, 1kHz) threshold current of 40mA, which yields a threshold current density of 3kA/cm² (see FIG. 5). More than 30% reduction in the light output power results from 300Å thick Ag barrier layer in this sample, and the blocking by a probe itself. The light output power at 140mA is 6.5mW.

Claims

1. A semiconductor vertical cavity surface emitting laser (10) comprising a semiconductor body which comprises a plurality of layers selected from GaAs, InP, InGaAs, InGaPAs, AlAs, AlGaAs, AlGaInAs and other related group III-V and group II-VI compound semiconductors, said plurality of layers including,
 - an active region (15) which generates optical radiation,
 - a bottom multilayer mirror (13) which reflects said radiation,
 - a top multilayer mirror (17) which partially reflects and partially transmits said radiation in a direction perpendicular to the active region, said top mirror including an ion-implanted region (18) arranged peripherally in the layers of the top mirror and defining a window (19) for confining passage of current and of lasing emission to an area defined by the window,
 - a dielectric layer (20) upon the top mirror, said dielectric layer having a window (21) aligned with the window in the ion-implanted region,
 - a metallic barrier layer (22) upon the dielectric layer and contacting that surface of the top mirror layer which is exposed in the window of the dielectric mirror layer,
 - a layer of an optically transparent semiconductor material (23) on the metal barrier layer forming a top electrode of the laser, said optically transparent layer having conductivity ranging from 1×10³ to 1×10⁵Ω⁻¹cm⁻¹, emitted laser light transmissivity of at least 80 percent and absorp-



which is exposed in window 21 are plasma cleaned, a silver layer, from 10 to 50 Å thick, is deposited (preferably by evaporation) upon the SiO₂ layer and also on the exposed surface of the top mirror.

Electrode 23 of cadmium tin oxide (or indium tin oxide) is formed on top of barrier electrode 22 with a thickness from about 50 to 500 nm, preferably 200 to 300 nm. In this thickness range, electrode 23 is sufficiently optically transparent to the lasing emission enabling its use as a top electrode of the VCSEL. Thicknesses higher than 500 nm may result in an increased series resistance without any improvement in the lasing efficiency.

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Claims

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 - an active region (15) which generates optical radiation,
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 - a dielectric layer (20) upon the top mirror, said dielectric layer having a window (21) aligned with the window in the ion-implanted region,
 - a metallic barrier layer (22) upon the dielectric layer and contacting that surface of the top mirror layer which is exposed in the window of the dielectric mirror layer,
 - a layer of an optically transparent semiconductor material (23) on the metal barrier layer forming a top electrode of the laser, said optically transparent layer having conductivity ranging from 1×10³ to 1×10⁵Ω⁻¹cm⁻¹, emitted laser light transmissivity of at least 80 percent and absorp-



tion of less than 10 percent and a bottom electrode (11) for applying in conjunction with the top electrode an excitation current in direction substantially perpendicular to the main plane of the active region and substantially parallel to the direction of propagation of optical radiation.

2. The laser of claim 1, in which said optically transparent semiconductor material of the top electrode is selected from the group consisting of cadmium tin oxide and indium tin oxide.
3. The laser of claim 2 in which the thickness of said top electrode ranges from 50 to 500 nm.
4. The laser of claim 2 in which the thickness of said top electrode ranges from 200 to 300 nm.
5. The laser of claim 1, in which the metal of the metallic barrier layer is selected from the group consisting of Ag, Au, AuBe, AuZn, Cr, Ti.
6. The laser of claim 5, in which said metal is silver.
7. The laser of claim 6, in which the thickness of the silver layer ranges from 10 to 50 Å.
8. The laser of claim 1, in which said dielectric material is selected from the group consisting of SiO_2 , Si_3N_4 , and Vycor® glass.
9. The laser of claim 8, in which said dielectric material is SiO_2 deposited in a thickness of from 0.01 to 0.1 µm.
10. The laser of claim 1, in which said bottom mirror is a multilayer distributed Bragg reflection mirror comprising from 10 to 40 periods.
11. The laser of claim 10 in which said bottom mirror is a 30 period structure.
12. The laser of claim 11, in which said active region is GaAs, and each of said periods comprises a pair of quarterwave layers selected from AlAs and GaAs and from AlAs and $\text{Al}_{0.05}\text{Ga}_{0.95}\text{As}$.
13. The laser of claim 12, in which said active layer is GaAs, and each of said periods is of a structure which includes $\text{Al}_{0.14}\text{Ga}_{0.86}\text{As}, 500\text{Å}/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}, 100\text{Å}/\text{AlAs}, 580\text{Å}/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}, 100\text{Å}$.
14. The laser of claim 12, in which said mirror structure is linearly graded.
15. The laser of claim 12, in which said mirror structure is a superlattice graded structure.

16. The laser of claim 1, in which said top mirror is one-step graded multilayer distributed Bragg reflection mirror comprising from 2 to 20 periods.

- 5 17. The laser of claim 16, in which said active layer is GaAs and each of said periods of the mirror is of a structure which includes $\text{Al}_{0.14}\text{Ga}_{0.86}\text{As}, 500\text{Å}/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}, 100\text{Å}/\text{AlAs}, 580\text{Å}/\text{Al}_{0.57}\text{Ga}_{0.43}\text{As}, 100\text{Å}$.
- 10 18. The laser of claim 1, in which said ion-implanted region includes ions selected from H^+ and O^+ .
- 15 19. The laser of claim 18, in which said ion is H^+ .

Patentansprüche

1. Oberflächenemittierender Halbleiterlaser (10) mit vertikaler Kavität mit einem Halbleiterkörper, der eine Vielzahl von Schichten umfaßt, die ausgewählt sind aus GaAs, InP, InGaAs, InGaPAs, AlAs, AlGaAs, AlGaInAs und anderen verwandten Verbindungshalbleitern der Gruppe III-V und der Gruppe II-VI, wobei die Vielzahl von Schichten umfaßt:
 - einen aktiven Bereich (15), der optische Strahlung erzeugt,
 - einen Mehrlagen-Bodenspiegel (13), der die Strahlung reflektiert,
 - einen oberen Mehrlagen-Spiegel (17), der die Strahlung in einer Richtung senkrecht zum aktiven Bereich teilweise durchläßt und teilweise reflektiert, wobei der obere Spiegel einen ionenimplantierten Bereich (18) umfaßt, der in den Schichten des oberen Spiegels am Umfang angeordnet ist und ein Fenster (19) definiert, um den Durchtritt von Strom und von Laseremission auf einen durch das Fenster definierten Bereich einzuschließen,
 - eine dielektrische Schicht (20) auf dem oberen Spiegel, wobei die dielektrische Schicht ein zu dem Fenster in den Ionenimplantierten Bereich ausgerichtetes Fenster (21) hat,
 - eine metallische Barrierenschicht (22), die auf der dielektrischen Schicht ist und die Oberfläche der oberen Spiegelschicht kontaktiert, die im Fenster der dielektrischen Spiegelschicht freiliegt,
 - eine Schicht aus einem optisch transparenten Halbleitermaterial (23) auf der Metallbarrierenschicht, die eine obere Elektrode des Lasers ausbildet, wobei die optisch transparente Schicht eine spezifische Leitfähigkeit im Bereich von 1×10^3 bis $1 \times 10^5 \Omega^{-1} \text{cm}^{-1}$ hat, eine Lichtdurchlässigkeit für emittiertes Laserlicht von wenigstens 80 % und eine Absorption von weniger als 10 % hat und mit
 - einer Bodenelektrode (11) zum Anlegen



eines Anregungsstroms zusammen mit der oberen Elektrode in einer im wesentlichen senkrechten Richtung zur Hauptebene des aktiven Bereichs und im wesentlichen parallel zur Richtung der Ausbreitung der optischen Strahlung.

2. Laser nach Anspruch 1, in welchem das optisch transparente Halbleitermaterial der oberen Elektrode aus der aus Cadmiumzinnoxid und Indiumzinnoxid bestehenden Gruppe ausgewählt ist.
3. Laser nach Anspruch 2, in welchem die Dicke der oberen Elektrode von 50 bis 500 nm reicht.
4. Laser nach Anspruch 2, in welchem die Dicke der oberen Elektrode von 200 bis 300 nm reicht.
5. Laser nach Anspruch 1, in welchem das Metall der metallischen Barrierschicht aus der Gruppe ausgewählt ist, die aus Ag, Au, AuBe, AuZn, Cr, Ti besteht.
6. Laser nach Anspruch 5, in welchem das Metall Silber ist.
7. Laser nach Anspruch 6, in welchem die Dicke der Silberschicht von 10 bis 50 Å reicht.
8. Laser nach Anspruch 1, in welchem das dielektrische Material aus der Gruppe ausgewählt ist, die aus SiO_2 , Si_3N_4 und Vycor[®]-Glas besteht.
9. Laser nach Anspruch 8, in welchem das dielektrische Material in einer Dicke von 0,01 bis 0,1 µm abgeschiedenes SiO_2 ist.
10. Laser nach Anspruch 1, in welchem der Bodenspiegel ein Mehrlagen-Spiegel mit verteilter Bragg-Reflexion mit von 10 bis 40 Perioden ist.
11. Laser nach Anspruch 10, in welchem der Bodenspiegel eine Struktur mit 30 Perioden ist.
12. Laser nach Anspruch 11, in welchem der aktive Bereich GaAs ist und jede Periode ein Paar von Viertel-Wellenlängenschichten umfaßt, die aus AlAs und GaAs und aus AlAs und $\text{Al}_{0,05}\text{Ga}_{0,95}\text{As}$ ausgewählt sind.
13. Laser nach Anspruch 12,

in welchem die aktive Schicht GaAs ist und jede Periode eine Struktur enthält, die $\text{Al}_{0,14}\text{Ga}_{0,86}\text{As}$, 500 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å/AlAs, 580 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å enthält.

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14. Laser nach Anspruch 12, in welchem die Spiegelstruktur einen linearen Gradienten hat.
15. Laser nach Anspruch 12, in welchem die Spiegelstruktur eine Gradienten-Übergitter-Struktur ist.
16. Laser nach Anspruch 1, in welchem der obere Spiegel ein einstufiger Gradienten-Mehrlagen-Spiegel mit verteilter Bragg-Reflexion von 2 bis 20 Perioden ist.
17. Laser nach Anspruch 16, in welchem die aktive Schicht GaAs ist und jede Periode des Spiegels aus einer Struktur besteht, die $\text{Al}_{0,14}\text{Ga}_{0,86}\text{As}$, 500 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å/AlAs, 580 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å enthält.
18. Laser nach Anspruch 1, in welchem der ionenimplantierte Bereich aus H^+ und O^+ ausgewählte Ionen enthält.
19. Laser nach Anspruch 18, in welchem das Ion H^+ ist.

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Revendications

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1. Laser (10) à semi-conducteurs à cavité verticale à émission de surface comprenant un corps semi-conducteur qui se compose d'une pluralité de couches choisies parmi GaAs, InP, InGaAs, InGaPAs, AlAs, AlGaAs, AlGaInAs et d'autres composés semi-conducteurs apparentés des groupes III-V et II-VI, ladite pluralité de couches comprenant :
 - une région active (15) qui génère un rayonnement optique;
 - un miroir multicouche inférieur (13) qui reflète ledit rayonnement;
 - un miroir multicouche supérieur (17) qui reflète partiellement et transmet partiellement ledit rayonnement dans une direction perpendiculaire à la région active, ledit miroir supérieur comprenant une région à implantation d'ions (18) disposée périphériquement dans les couches du miroir supérieur et définissant une fenêtre (19) pour confiner le passage du courant et de l'émission laser à un domaine défini par la fenêtre;
 - une couche diélectrique (20) au-dessus du miroir supérieur, ladite couche diélectrique possédant une fenêtre (21) dans l'alignement de



la fenêtre de la région à implantation d'ions;
une couche de barrage métallique (22) au-dessus de la couche diélectrique et en contact avec la surface de la couche du miroir supérieur qui est exposée dans la fenêtre de la couche diélectrique du miroir;

une couche d'un matériau semi-conducteur optiquement transparent (23) sur la couche de barrage métallique formant une électrode supérieure du laser, ladite couche optiquement transparente possédant une conductivité allant de 1×10^3 à $1 \times 10^5 \Omega^{-1} \text{cm}^{-1}$, une transmissivité de la lumière laser émise d'au moins 80 pour cent et une absorption de moins de 10 pour cent, et

une électrode inférieure (11) pour appliquer, conjointment avec l'électrode supérieure, un courant d'excitation dans une direction en substance perpendiculaire au plan principal de la région active et en substance parallèle à la direction de propagation du rayonnement optique.

2. Laser selon la revendication 1, dans lequel ledit matériau semi-conducteur optiquement transparent de l'électrode supérieure est choisi dans le groupe composé de l'oxyde de cadmium et d'étain et de l'oxyde d'indium et d'étain.
3. Laser selon la revendication 2, dans lequel l'épaisseur de ladite électrode supérieure va de 50 à 500 nm.
4. Laser selon la revendication 2, dans lequel l'épaisseur de ladite électrode supérieure va de 200 à 300 nm.
5. Laser selon la revendication 1, dans lequel le métal de la couche de barrage métallique est choisi dans le groupe composé d'Ag, Au, AuBe, AuZn, Cr, Ti.
6. Laser selon la revendication 5, dans lequel ledit métal est l'argent.
7. Laser selon la revendication 6, dans lequel l'épaisseur de la couche d'argent va de 10 à 50 Å.
8. Laser selon la revendication 1, dans lequel ledit matériau diélectrique est choisi dans le groupe composé du SiO_2 , du Si_3N_4 et du verre Vycor®.
9. Laser selon la revendication 8, dans lequel ledit matériau diélectrique est du SiO_2 déposé en une épaisseur de 0,01 à 0,1 μm .
10. Laser selon la revendication 1, dans lequel ledit miroir inférieur est un miroir multicouche à ré-

flexion de Bragg distribuée comprenant de 10 à 40 périodes.

- 5 11. Laser selon la revendication 10, dans lequel ledit miroir inférieur est une structure à 30 périodes.
- 10 12. Laser selon la revendication 11, dans lequel ladite région active est du GaAs et chacune desdites périodes comprend une paire de couches quart d'onde choisies parmi AlAs et $\text{Al}_{0,05}\text{Ga}_{0,95}\text{As}$.
- 15 13. Laser selon la revendication 12, dans lequel ladite couche active est GaAs et chacune desdites périodes présente une structure comprenant $\text{Al}_{0,14}\text{Ga}_{0,86}\text{As}$, 500 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å/AlAs, 580 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å.
- 20 14. Laser selon la revendication 12, dans lequel ladite structure de miroir est à gradation linéaire.
- 25 15. Laser selon la revendication 12, dans lequel ladite structure de miroir est une structure à gradation de superréseau.
- 30 16. Laser selon la revendication 1, dans lequel ledit miroir supérieur est un miroir multicouche à réflexion de Bragg distribuée à gradation d'un pas comprenant de 2 à 20 périodes.
- 35 17. Laser selon la revendication 16, dans lequel ladite couche active est du GaAs et chacune desdites périodes du miroir présente une structure comprenant $\text{Al}_{0,14}\text{Ga}_{0,86}\text{As}$, 500 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å/AlAs, 580 Å/ $\text{Al}_{0,57}\text{Ga}_{0,43}\text{As}$, 100 Å.
- 40 18. Laser selon la revendication 1, dans lequel la région à implantation d'ions comprend des ions choisis dans le groupe composé de H^+ et O^+ .
- 45 19. Laser selon la revendication 18, dans lequel ledit ion est H^+ .